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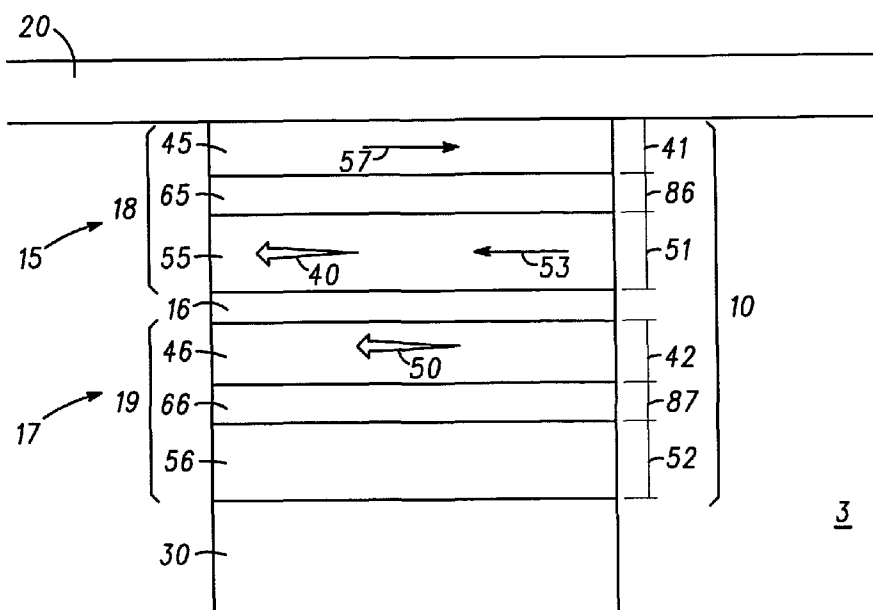
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(54) Title: WRITING TO A SCALABLE MRAM ELEMENT



(57) Abstract: A method to switch a scalable magnetoresistive memory cell (10) including the steps of providing a magnetoresistive memory device (3) sandwiched between a word line (20) and a digit line (30) so that current waveforms can be applied to the word and digit lines at various times to cause a magnetic field flux to rotate the effective magnetic moment vector of the device by approximately 180°. The magnetoresistive memory device includes N ferromagnetic layers that are anti-ferromagnetically coupled. N can be adjusted to change the magnetic switching volume of the device.



WO 03/034437 A2



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